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Vishay/Siliconix SQM40N15-38-GE3

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Datasheet of SQM40N15-38-GE3 - MOSFET N-CH 150V 40A TO263

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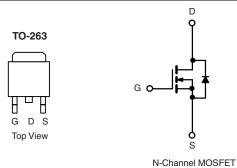




Vishay Siliconix

Automotive N-Channel 150 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	150			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.038			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 6 \text{ V}$	0.040			
I _D (A)	40			
Configuration	Single			



Halogen-free According to IEC 61249-2-21 Definition

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified^d

FEATURES

- 100 % R_q and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM40N15-38-GE3

ABSOLUTE MAXIMUM RATINGS (To	_C = 25 °C, unles	s otherwise noted	l)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage	V _{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C	1	40	
Continuous Drain Current	T _C = 125 °C	- I _D	23	
Continuous Source Current (Diode Conduction)a	I _S	100	А	
Pulsed Drain Current ^b	I _{DM}	80		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	40	
Single Pulse Avalanche Energy	L=0.11III	E _{AS}	80	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	Б	166	W
	T _C = 125 °C	P_{D}	55	VV
Operating Junction and Storage Temperature Ran	ge	T _J , T _{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient F	PCB Mount ^c	R _{thJA}	40	°C/W		
Junction-to-Case (Drain)		R _{thJC}	0.9	C/VV		

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static		•					
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		150	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.5	3.0	3.5	\ \
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 150 V	-	-	1.0	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 150 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 150 V, T _J = 175 °C	-	-	250	<u> </u>
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α
		V _{GS} = 10 V	I _D = 15 A	-	0.027	0.038	Ω
		V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.078	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.105	
		V _{GS} = 6 V	I _D = 10 A	-	0.030	0.040	
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		-	40	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	2710	3390	
Output Capacitance	Coss	$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = 25 V, f = 1 MHz		310	390	pF
Reverse Transfer Capacitance	C _{rss}	1		-	130	165	1
Total Gate Charge ^c	Qg			-	46	70	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 75 \text{ V}, I_{D} = 85 \text{ A}$	-	20	-	nC
Gate-Drain Charge ^c	Q_{gd}	1		-	11	-	
Gate Resistance	R_g	f = 1 MHz		1	2	3	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	14	21	
Rise Time ^c	t _r	V_{DD} = 75 V, R_L = 0.88 Ω I_D \cong 85 A, V_{GEN} = 10 V, R_g = 1 Ω		-	17	26	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	24	36	
Fall Time ^c	t _f			-	9	14	1
Source-Drain Diode Ratings and Chara	acteristics ^b	•				•	
Pulsed Current ^a	I _{SM}			-	-	80	Α
Forward Voltage	V_{SD}	$I_F = 85 \text{ A}, V_{GS} = 0$		-	0.95	1.5	V

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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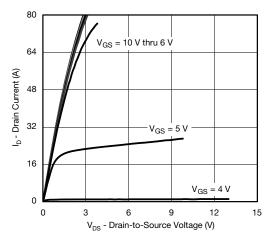
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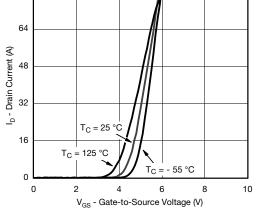
SQM40N15-38

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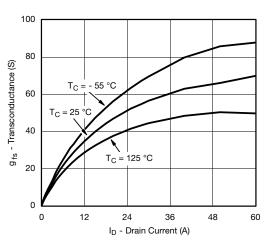
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



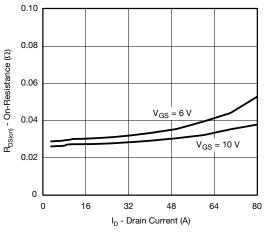
Output Characteristics



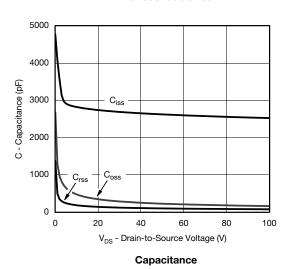
Transfer Characteristics

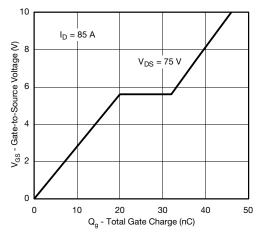


Transconductance



On-Resistance vs. Drain Current





Gate Charge

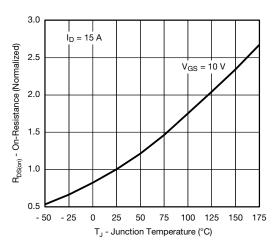
S11-2035-Rev. C, 17-Oct-11 3 Document Number: 65269



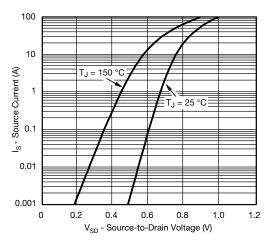
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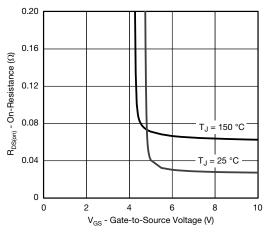
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



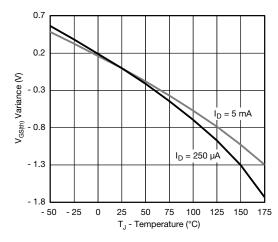
On-Resistance vs. Junction Temperature



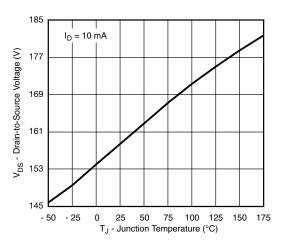
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

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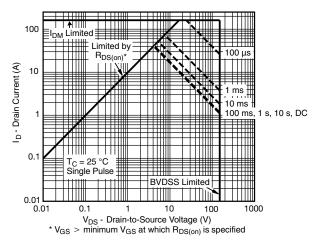
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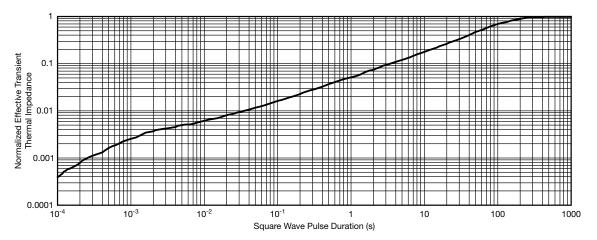
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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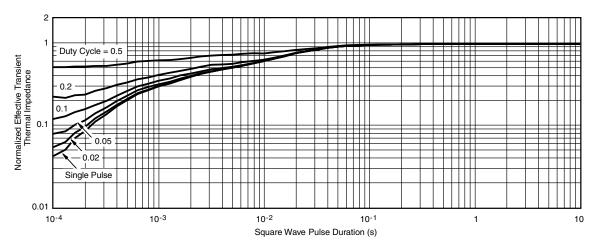
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- · The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65269.

Datasheet of SQM40N15-38-GE3 - MOSFET N-CH 150V 40A TO263

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Ordering Information

Vishay Siliconix

D²PAK / TO-263 and TO-262

Ordering codes for the SQ rugged series power MOSFETs in the D2PAK / TO-263 and TO-262 packages:

DATASHEET PART NUMBER	OLD ORDERING CODE a	NEW ORDERING CODE	
SQM100N04-2m7	SQM100N04-2M7-GE3	SQM100N04-2M7_GE3	
SQM100N10-10	SQM100N10-10-GE3	SQM100N10-10_GE3	
SQM110N05-06L	SQM110N05-06L-GE3	SQM110N05-06L_GE3	
SQM110P06-8m9L	SQM110P06-8M9L-GE3	SQM110P06-8M9L_GE3	
SQM120N02-1m3L	SQM120N02-1M3L-GE3	SQM120N02-1M3L_GE3	
SQM120N03-1m5L	SQM120N03-1M5L-GE3	SQM120N03-1M5L_GE3	
SQM120N04-1m7	SQM120N04-1M7-GE3	SQM120N04-1M7_GE3	
SQM120N04-1m7L	SQM120N04-1M7L-GE3	SQM120N04-1M7L_GE3	
SQM120N04-1m9	SQM120N04-1M9-GE3	SQM120N04-1M9_GE3	
SQM120N06-06	SQM120N06-06-GE3	SQM120N06-06_GE3	
SQM120N06-3m5L	SQM120N06-3M5L-GE3	SQM120N06-3M5L_GE3	
SQM120N10-09	SQM120N10-09-GE3	SQM120N10-09_GE3	
SQM120N10-3m8	SQM120N10-3M8-GE3	SQM120N10-3M8_GE3	
SQM120P04-04L	SQM120P04-04L-GE3	SQM120P04-04L_GE3	
SQM120P06-07L	SQM120P06-07L-GE3	SQM120P06-07L_GE3	
SQM120P10-10m1L	-	SQM120P10_10m1LGE3	
SQM200N04-1m1L	SQM200N04-1M1L-GE3	SQM200N04-1M1L_GE3	
SQM200N04-1m7L	SQM200N04-1M7L-GE3	SQM200N04-1M7L_GE3	
SQM200N04-1m8	SQM200N04-1M8-GE3	SQM200N04-1M8_GE3	
SQM25N15-52	SQM25N15-52-GE3	SQM25N15-52_GE3	
SQM35N30-97	SQM35N30-97-GE3	SQM35N30-97_GE3	
SQM40010EL	-	SQM40010EL_GE3	
SQM40N10-30	SQM40N10-30-GE3	SQM40N10-30_GE3	
SQM40N15-38	SQM40N15-38-GE3	SQM40N15-38_GE3	
SQM40P10-40L	SQM40P10-40L-GE3	SQM40P10-40L_GE3	
SQM47N10-24L	SQM47N10-24L-GE3	SQM47N10-24L_GE3	
SQM50020EL	-	SQM50020EL_GE3	
SQM50N04-4m0L	SQM50N04-4M0L-GE3	SQM50N04-4M0L_GE3	
SQM50N04-4m1	SQM50N04-4M1-GE3	SQM50N04-4M1_GE3	
SQM50P03-07	SQM50P03-07-GE3	SQM50P03-07_GE3	
SQM50P04-09L	SQM50P04-09L-GE3	SQM50P04-09L_GE3	
SQM50P06-15L	SQM50P06-15L-GE3	SQM50P06-15L_GE3	
SQM50P08-25L	SQM50P08-25L-GE3	SQM50P08-25L_GE3	
SQM60030E	-	SQM60030E_GE3	
SQM60N06-15	SQM60N06-15-GE3	SQM60N06-15_GE3	
SQM60N20-35	SQM60N20-35-GE3	SQM60N20-35_GE3	
SQM70060EL	-	SQM70060EL_GE3	
SQM85N15-19	SQM85N15-19-GE3	SQM85N15-19_GE3	
SQV120N10-3m8	SQV120N10-3m8-GE3	SQV120N10-3m8_GE3	
SQV120N06-4m7L	-	SQV120N06-4m7L GE3	

Note

Revision: 06-Jul-16 1 Document Number: 67164

a. Old ordering code is obsolete and no longer valid for new orders

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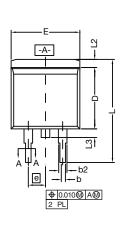
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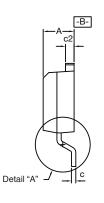


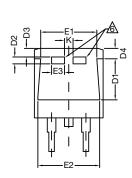
Package Information

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TO-263 (D²PAK): 3-LEAD

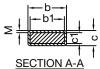








DETAIL A (ROTATED 90°)



<u> </u>	b1	ļ	1
< T		10	ပ
<u>s</u>	ECTION	1 <u>A-A</u>	Ť

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.

6. This feature is for thick lead.

		INC	HES	MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
	L2	0.040	0.055	1.016	1.397	
	L3	0.050	0.070	1.270	1.778	
L4		0.010	0.010 BSC		BSC	
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843

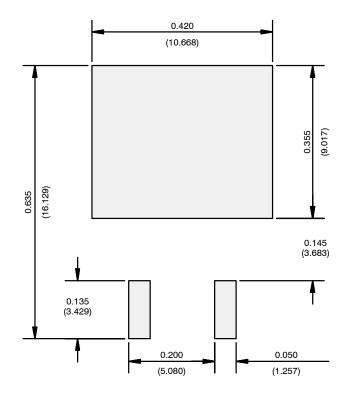
Revison: 30-Sep-13 Document Number: 71198 1





AN826 Vishay Siliconix

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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Document Number: 73397 www.vishay.com 11-Apr-05



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Revision: 13-Jun-16 1 Document Number: 91000